DUAL 2 TO 4 DECODER/DEMULTIPLEXER

- HIGH SPEED
 - $t_{PD} = 12 \text{ ns} (TYP.) AT V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION $I_{CC} = 4 \mu A \text{ (MAX.)} \text{ AT } T_A = 25 \text{ °C}$
- HIGH NOISE IMMUNITY

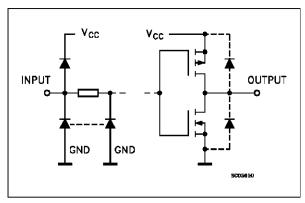
 VNIH = VNIL = 28 % VCC (MIN.)
- OUTPUT DRIVE CAPABILITY
 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE ||OH| = |OL| = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS tplh = tphl
- WIDE OPERATING VOLTAGE RANGE Vcc (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS139

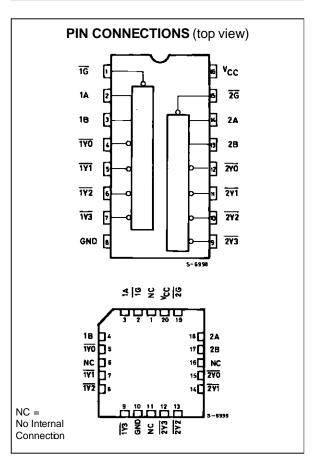
B1R F1R (Ceramic Package) M1R (C1R (Micro Package) (Chip Carrier) ORDER CODES: M54HC139F1R M74HC139M1R M74HC139B1R M74HC139C1R

DESCRIPTION

The M54/74HC139 is a high speed CMOS DUAL TWO LINE TO FOUR LINE DECODER/DEMULTI-PLEXER fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. The active low enable input can be used for gating or as a data input for demultiplexing applications. While the enable input is held high, all four outputs are high independently of the other inputs. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT





February 1993

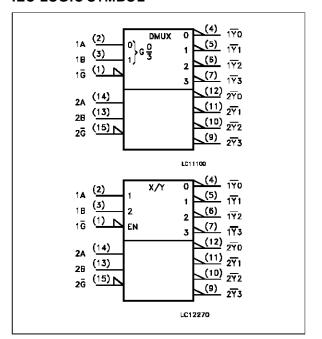
TRUTH TABLE

INP	UTS			OUTI	PUTS		SELECTED
ENABLE	SEL	ECT	\overline{Y}_0	_ 7₁	\overline{Y}_2	\overline{Y}_3	OUTPUT
G	В	Α	10	'1	12	13	
Н	Х	Χ	Η	Н	Н	Н	NONE
L	L	L	L	Н	Н	Н	\overline{Y}_0
L	L	Н	Н	L	Н	Н	\overline{Y}_1
L	Н	L	Н	Н	L	Н	\overline{Y}_2
L	Н	Н	Н	Н	Н	L	\overline{Y}_3

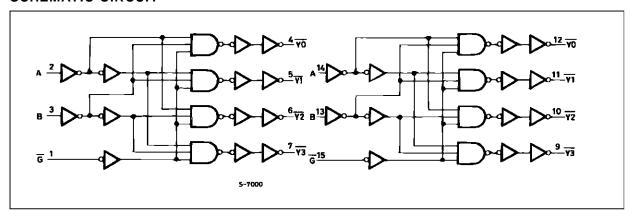
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 15	1G, 2G	Enable Inputs
2, 3	1A, 1B	Address Inputs
4, 5, 6, 7	$1\overline{Y}_0$ to $1\overline{Y}_3$	Outputs
12, 11, 10, 9	$2\overline{Y}_0$ to $2\overline{Y}_3$	Outputs
14, 13	2A, 2B	Address Inputs
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

IEC LOGIC SYMBOL



SCHEMATIC CIRCUIT



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
l _{IK}	DC Input Diode Current	± 20	mA
lok	DC Output Diode Current	± 20	mA
Ιο	DC Output Source Sink Current Per Output Pin	± 25	mA
Icc or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P_{D}	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T∟	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. (*) 500 mW: ≅ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C



RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
Vcc	Supply Voltage		2 to 6	V
V_{I}	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature: M54HC Series M74HC Series		-55 to +125 -40 to +85	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 2 V	0 to 1000	ns
		$V_{CC} = 4.5 \text{ V}$	0 to 500	
		$V_{CC} = 6 V$	0 to 400	

DC SPECIFICATIONS

		Test Conditions			Value							
Symbol	Parameter	V _{CC}			T _A = 25 °C 54HC and 74HC			1	85 °C HC	-55 to 125 °C 54HC		Unit
		(۷)			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input	2.0			1.5			1.5		1.5		
	Voltage	4.5			3.15			3.15		3.15		V
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input	2.0					0.5		0.5		0.5	
	Voltage	4.5					1.35		1.35		1.35	V
		6.0					1.8		1.8		1.8	
V _{OH} High Level	High Level	2.0	V _I =		1.9	2.0		1.9		1.9		
	Output Voltage	4.5	VI – VIH	I _O =-20 μA	4.4	4.5		4.4		4.4		.,
		6.0	or		5.9	6.0		5.9		5.9		V
		4.5	VIL	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output	2.0	Vı =			0.0	0.1		0.1		0.1	
	Voltage	4.5	VI =	I _O = 20 μA		0.0	0.1		0.1		0.1	
		6.0	or			0.0	0.1		0.1		0.1	V
		4.5	V _{IL}	I _O = 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I _O = 5.2 mA		0.18	0.26		0.33		0.40	
lį	Input Leakage Current	6.0	V _I = '	Vcc or GND			±0.1		±1		±1	μΑ
Icc	Quiescent Supply Current	6.0	V _I = '	V _{CC} or GND			4		40		80	μΑ



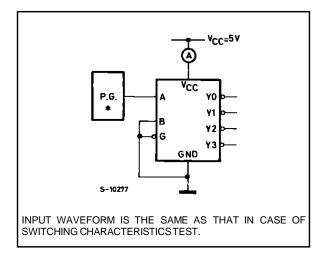
AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

		Tes	t Conditions	Value							
Symbol	Parameter	ACC		T _A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH}	Output Transition	2.0			30	75		95		110	
t _{THL}	Time	4.5			8	15		19		22	ns
		6.0			7	13		16		19	
t _{PLH}	Propagation	2.0			45	130		165		195	
t _{PHL}	Delay Time	4.5			15	26		33		39	ns
	(A, B - Y)	6.0			13	22		28		33	
t _{PLH}	Propagation	2.0			39	110		140		165	
t_{PHL}	Delay Time	4.5			13	22		28		33	ns
(G - Y)	6.0			11	19		24		28		
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{PD} (*)	Power Dissipation Capacitance				46						pF

^(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}$

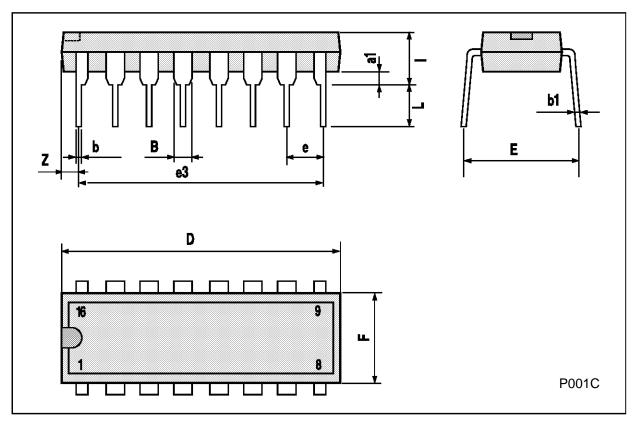
SWITCHING CHARACTERISTICS TEST CIRCUIT

TEST CIRCUIT Icc (Opr.)



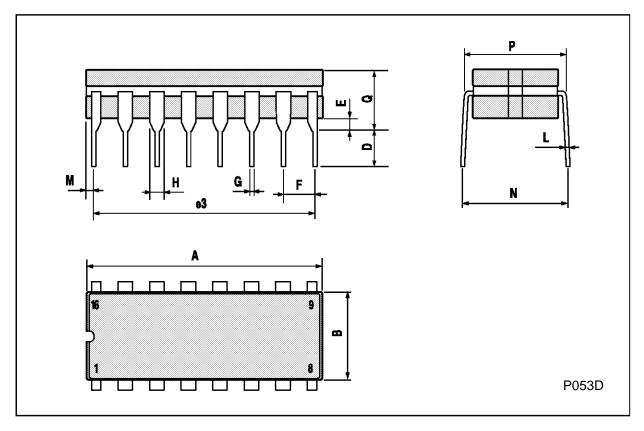
Plastic DIP16 (0.25) MECHANICAL DATA

DIM.		mm			inch			
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		



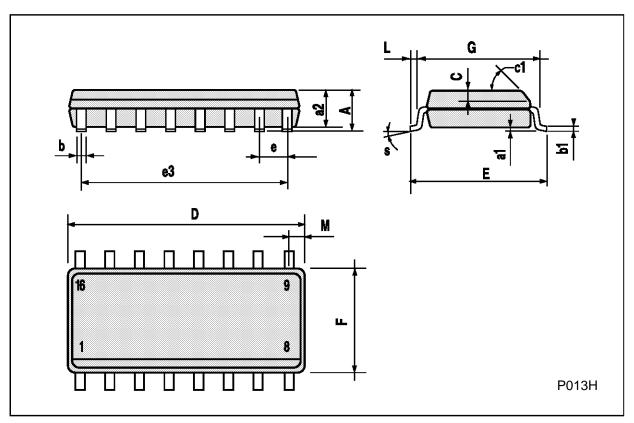
Ceramic DIP16/1 MECHANICAL DATA

DIM.		mm			inch	
Dilli.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			20			0.787
В			7			0.276
D		3.3			0.130	
Е	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
Н	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
Р	7.8		8.05	0.307		0.317
Q			5.08			0.200



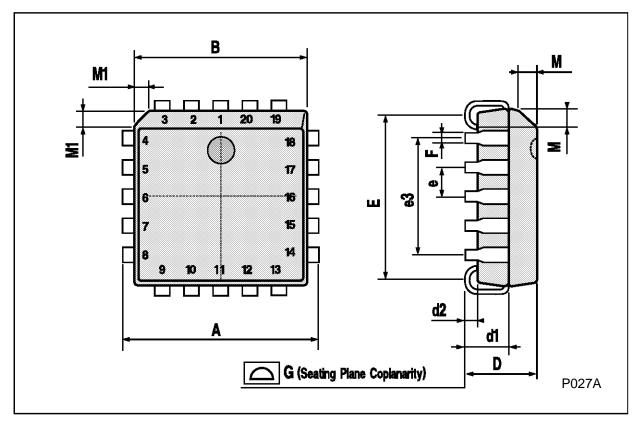
SO16 (Narrow) MECHANICAL DATA

DIM.		mm			inch	
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1			45°	(typ.)		
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.62			0.024
S			8° (ı	max.)		



PLCC20 MECHANICAL DATA

DIM.		mm		inch			
Dilli.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	9.78		10.03	0.385		0.395	
В	8.89		9.04	0.350		0.356	
D	4.2		4.57	0.165		0.180	
d1		2.54			0.100		
d2		0.56			0.022		
E	7.37		8.38	0.290		0.330	
е		1.27			0.050		
e3		5.08			0.200		
F		0.38			0.015		
G			0.101			0.004	
М		1.27			0.050		
M1		1.14			0.045		



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